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#6/Amend B  
Patents  
4/16/02

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

**Applicant(s):** Noriaki Oda, et al.

**Examiner:** Monica Lewis

**Serial No:** 09/863,737

**Art Unit:** 2822

**Filed:** May 23, 2001

**Docket:** 12562A

**For:** SEMICONDUCTOR DEVICE AND  
METHOD FOR MANUFACTURING  
THE SAME

**Dated:** May 15, 2002

Assistant Commissioner for Patents  
Washington, D.C. 20231

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**RESPONSE**

Sir:

In response to the Office Action dated January 15, 2002, applicants submit the following Amendment for entry in the above-identified application.

**IN THE SPECIFICATION:**

Please amend the specification as follows:

Replace the paragraph that begins on Page 2, line 28 with the following:

Subsequently, as shown in Fig. 1, a third interlayer insulating film 17 having a viahole 18 is formed, a tungsten plug 19 is formed in the viahole 18, and a barrier metal layer 5C, an aluminum layer 6C and a titanium nitride layer 7C are successively formed. Thereafter, a desired pattern is left to form the third layer wiring 20. Then, a cover film 21 is formed, thereby completing the final structure shown in Fig. 1.

**CERTIFICATE OF MAILING UNDER 37 C.F.R. §1.8(a)**

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231, on May 15, 2002.

Dated: May 15, 2002

Lisa Fiumara